

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	"235"/\$.ccls. and card and ((compar\$4 with time) same (disable with card with time))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:14
S2	1	"235"/\$.ccls. and ((compar\$4 with time) same (disable with card with time))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:14
S3	8	((compar\$4 with time) same (disable with card with time))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:14
S4	16	((compar\$4 with time) same (disable with card))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:16
S5	8	S4 not S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:16
S6	47	((compar\$4 with time) same (disabl\$4 with card))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:20
S7	31	S6 not S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:20
S8	212	(measur\$4 with residual with charge with capacit\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:43

S9	20	(measur\$4 with residual with charge with capacit \$4) near10 time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:43
S10	359	(residual with charge with capacit \$4) near10 time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:48
S11	741	(residual with charge with capacit \$4 with time)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:48
S12	13	(residual with charge with capacit \$4 with (time near2 elapsed))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:48
S13	9	"6294997" and mos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:01
S14	2	"6294997".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:01
S15	435854	"235"/	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:03
S16	0	"235"/\$.ccls. and (card with cmos with capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:03
S17	0	"235"/\$.ccls. and (timing with cmos with capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:03
S18	0	"235"/\$.ccls. and (timing with mos with capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:03

S19	75	"235"/\$.ccls. and (mos with capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:03
S20	0	"235"/\$.ccls. and (mos with capacitor) same timing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:03
S21	0	"235"/\$.ccls. and (mos with capacitor) same timer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:03
S22	75	"235"/\$.ccls. and (mos with capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:03
S23	38	"235"/\$.ccls. and (mos with capacitor) and card	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:03
S24	0	"235"/\$.ccls. and (mos with capacitor) and pcmcia	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:04
S25	7	"235"/\$.ccls. and (mos with capacitor) and pcmcia	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:04
S26	30	(fet with insulative with layer) same (capacit\$4 with insulative with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:05
S27	0	(fet with insulative with layer) same (capacit\$4 with insulative with layer) and nanometer\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:05

S28	0	(fet with insulative with layer) same (capacit\$4 with insulative with layer) same nm	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:06
S29	0	(fet with insulative with layer) same (capacit\$4 with insulative with layer) and (nm or nanometer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:06
S30	29	(fet with insulative with layer) and (capacit\$4 with insulative with layer) and (nm or nanometer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:06
S31	0	(fet with insulative with layer) and ((capacit\$4 with insulative with layer) same (nm or nanometer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:06
S32	4	((field near3 effect) with insulative with layer) and ((capacit\$4 with insulative with layer) same (nm or nanometer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:08
S33	58	(mos with capacitor) and pcmcia	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:09
S34	23	(mosfet with insulat\$4 with layer) same (capacit\$4 with insulative with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:12
S35	7	S34 and (thickness with (nm or nanometer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:12

S36	0	(mosfet with insulat \$4 with layer) same (capacit\$4 with insulative with layer) same (greater or thicker)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 17:15
S37	3	((("4808802") or ("4710613") or ("5014311")).PN.	USPAT	OR	OFF	2009/02/28 17:52
S38	1	("5514995").PN.	USPAT	OR	OFF	2009/02/28 18:51

2/ 28/ 2009 7:03:08 PM

C:\ Documents and Settings\ kkoyama\ My Documents\ EAST\ Workspaces\ 10536493.w sp